



IXTX210P10T Information



For Reference Only

Part Number IXTX210P10T

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 100V 210A PLUS247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IXTX210P10T Specifications

Manufacturer Part NumberIXTX210P10TManufacturerIXYSCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-247-3SeriesTrenchP?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C210A (Tc)Drive Voltage (Max Rds On, Min Rds On)10V	
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-247-3 Series TrenchP? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-247-3 Series TrenchP? P-Channel 100V 100V 100V 100V	
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Drive Voltage (Max Rds On, Min Rds On) 10V	
Vgs(th) (Max) @ Id 4.5V @ 250μA	
Gate Charge (Qg) (Max) @ Vgs 740nC @ 10V	
Input Capacitance (Ciss) (Max) @ Vds 69500pF @ 25V	
Vgs (Max) ±15V	
FET Feature -	
Power Dissipation (Max) 1040W (Tc)	
Rds On (Max) @ Id, Vgs 7.5 mOhm @ 105A, 10V	
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	
Mounting Type Through Hole	
Supplier Device Package PLUS247?-3	
Package / Case TO-247-3	
Report	

IXTX210P10T Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTX210P10T Payment Methods



















IXTX210P10T Shipping Methods













If you have any question about IXTX210P10T, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com